

isc N-Channel MOSFET Transistor

2SK260

DESCRIPTION

- Drain Current $-I_D=5A @ T_C=25^\circ C$
- Drain Source Voltage-
: $V_{DSS}= 400V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

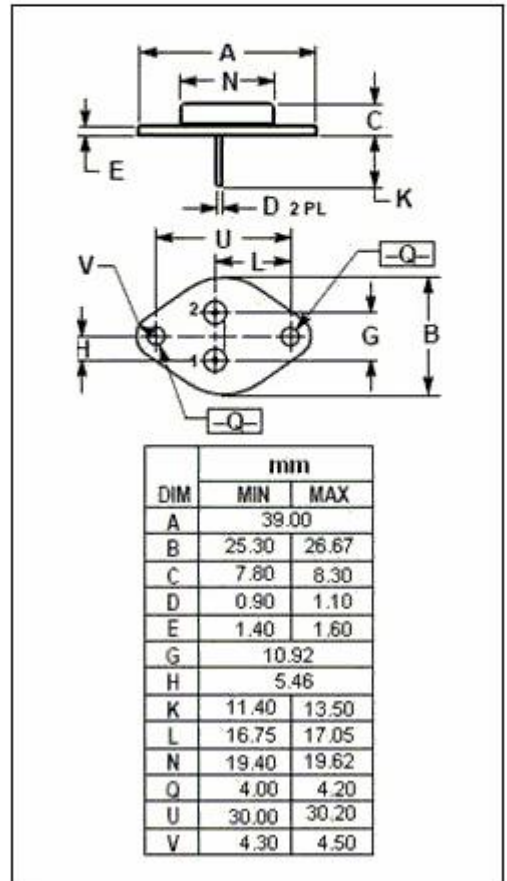
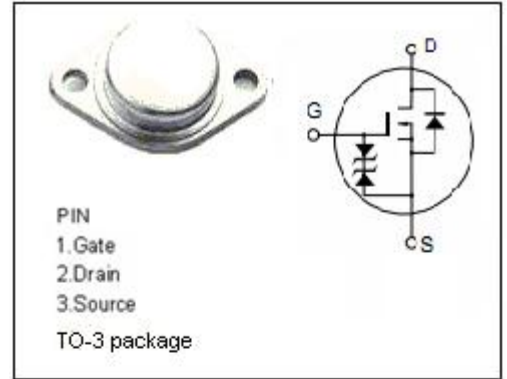
- Designed especially for high voltage,high speed applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	400	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^\circ C$	5	A
P_{tot}	Total Dissipation@ $TC=25^\circ C$	125	W
T_j	Max. Operating Junction Temperature	200	$^\circ C$
T_{stg}	Storage Temperature Range	-65~200	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.67	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^\circ C/W$



isc N-Channel Mosfet Transistor**2SK260****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	400			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = 10V _{GS} ; I _D = 10mA	0.4		3.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 15V; I _D = 3A		2.5	3.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±100	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =320V; V _{GS} = 0			1	mA
V _{DS(ON)}	Drain-Source Saturation Voltage	I _F = 3A; V _{GS} = 15V		7.5	9.5	V
ton	Turn-on time	V _{GS} =15V; I _D =2A; R _L =50 Ω		25		ns
toff	Turn-off time			140		ns